

P/1071-577

BARIUM TITANATE SEMICONDUCTIVE CERAMIC

ABSTRACT OF THE DISCLOSURE

The present invention provides barium titanate semiconductive ceramic having low specific resistance at room temperature and high withstand voltage, which fully satisfies the demand for enhancing withstand voltage. The average ceramic grain size of the barium titanate semiconductive ceramic is controlled to about 0.9 μm or less. By this control, the ceramic possesses low specific resistance at room temperature and high withstand voltage fully satisfying a recent demand for enhancing withstand voltage and may suitably used for applications such as controlling temperature and limiting current, or in exothermic devices for constant temperature. Accordingly, the barium titanate semiconductive ceramic enables an apparatus using the same to have enhanced performance and reduced size.

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7-2104082

SPBC1266084

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